

P.O. Box 747  
Falls Church, Virginia 22040-0747  
Phone: (703) 205-8000  
Fax: (703) 205-8050  
(703) 698-8590 (GIV)

**Birch, Stewart, Kolasch & Birch, LLP**

# Fax

<b>To:</b>	Examiner Williams/USPTO	<b>From:</b>	Tina R. Baker for Mr. Ken Muncy
<b>Fax:</b>	571-273-1924	<b>Date:</b>	August 25, 2004
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**Comments:**    **Per our telephone conversation today, please find attached a copy of the Abstract of the Specification in the above-referenced application for RUSH printing. Please call me at (703) 205-8000x6032, if you require anything further.**

Appl. No. 09/930,204  
Docket No.: 0941-0308P

## ABSTRACT OF THE DISCLOSURE

A protection circuit for MOS components. In the protection circuit, a bypass PMOS transistor has a gate, a source and a substrate, all coupled to a first voltage node and a drain coupled to a gate of a MOS component. A bypass NMOS transistor has a gate, a source and a substrate, all coupled to a second voltage node and a drain coupled to the gate of the MOS component. When positive charges are accumulated on the gate of the MOS component due to an antenna effect, the bypass PMOS transistor dissipates the positive charges to the first voltage node. On the contrary, when negative charges are accumulated on the gate of the MOS component due to antenna effect, the bypass NMOS transistor dissipates the negative charges to the second voltage node.